TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA2244FK

Low-Voltage Octal Bus Buffer with 3.6 V Tolerant Inputs and Outputs

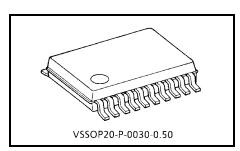
The TC7MA2244FK is a high performance CMOS octal bus buffer. Designed for use in $1.8~\rm V, 2.5~\rm V$ or $3.3~\rm V$ systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6~\mathrm{V}.$

This device is non-inverting 3-state buffer having four active-low output enables. When the \overline{ST} input is high, the outputs are in a high impedance state. This device is designed to be used with 3-state memory address drivers, etc.

The 26 Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.03 g (typ.)

Features

- 26 Ω series resistors on outputs.
- Low voltage operation: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation: $t_{pd} = 4.4 \text{ ns (max)} (V_{CC} = 3.0 \sim 3.6 \text{ V})$

 $t_{pd} = 5.6 \text{ ns (max) (VCC} = 2.3 \sim 2.7 \text{ V)}$

 $t_{pd} = 9.8 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $I_{OH}/I_{OL} = \pm 8 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

 $I_{OH}/I_{OL} = \pm 4 \text{ mA (min) (V}_{CC} = 1.8 \text{ V)}$

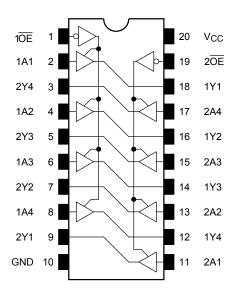
- Latch-up performance: -300 mA
- ESD performance: Machine model ≥ ±200 V

Human body model ≥ ±2000 V

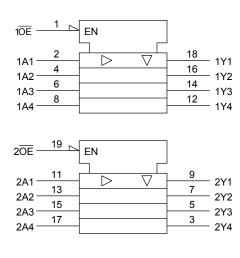
- Package: VSSOP (US)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)
 - *: To ensure the high-impedance state during power up or power down, $\overline{\sf OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

2007-10-19

Pin Assignment (top view)



IEC Logic Level



Truth Table

Inp	Outputs	
ŌĒ	A _n	Outputs
L	L	L
L	Н	Н
Н	Х	Z

X: Don't care

Z: High impedance

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	VIN	-0.5~4.6	V	
DC output voltage	Vout	-0.5~4.6 (Note 2)	V	
DC dulput voltage	VOU1	-0.5~V _{CC} + 0.5 (Note 3)]	
Input diode current	I _{IK}	-50	mA	
Output diode current	lok	±50 (Note 4)	mA	
DC output current	lout	±50	mA	
Power dissipation	PD	180	mW	
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA	
Storage temperature	T _{stg}	-65~150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Off-state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$



Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	1.8~3.6	
Supply voltage	VCC	1.2~3.6 (Note 2)	V
Input voltage	V _{IN}	-0.3~3.6	V
Output voltage	Vout	0~3.6 (Note 3)	V
Output voltage	VOU1	0~V _{CC} (Note 4)	V
		±12 (Note 5)	
Output current	I _{OH} /I _{OL}	±8 (Note 6)	mA
		±4 (Note 7)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

Note 3: Off-state

Note 4: High or low state Note 5: $V_{CC} = 3.0 \sim 3.6 \text{ V}$ Note 6: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 V$

Note 8: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = $-40\sim85^{\circ}$ C, 2.7 V < V_{CC} \leq 3.6 V)

Characteristics		Symbol	Test Condition			Min	Max	Unit
Characte	HSUCS	Symbol	yribbi Test Condition		V _{CC} (V)	IVIIII	IVIAX	Unit
Input voltage	High level	V _{IH}		_	2.7~3.6	2.0	_	V
iliput voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	٧
				$I_{OH} = -100 \mu A$	2.7~3.6	V _{CC} - 0.2	_	
	High level	Voн	VIN = VIH or VIL	$I_{OH} = -6 \text{ mA}$	2.7	2.2	_	
				$I_{OH} = -8 \text{ mA}$	3.0	2.4	_	
Output voltage				$I_{OH} = -12 \text{ mA}$	3.0	2.2	_	V
				$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2	
Low level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 6 mA	2.7	_	0.4		
			I _{OL} = 8 mA	3.0	_	0.55		
				I _{OL} = 12 mA	3.0	_	8.0	
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V	•	2.7~3.6	_	±5.0	μА
2 state output off	ntata aurrant	1	$V_{IN} = V_{IH}$ or V_{IL}		2.7~3.6		±10.0	
3-state output off-state current		loz	V _{OUT} = 0~3.6 V	V _{OUT} = 0~3.6 V		_	±10.0	μΑ
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА
			$V_{IN} = V_{CC}$ or GND		2.7~3.6	_	20.0	
Quiescent supply	current	ICC	I_{CC} $V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7~3.6	_	±20.0	μΑ
		Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$ (pe	er input)	2.7~3.6	_	750	



DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteristics		Symbol	Symbol Test Condition			Min	Max	Unit	
onarasts.		5,55.	rest condition		V _{CC} (V)			Offic	
Input voltage	High level	VIH		_	2.3~2.7	1.6	_	V	
input voltage	Low level	V _{IL}		_	2.3~2.7	_	0.7	V	
				$I_{OH} = -100 \mu A$	2.3~2.7	V _{CC} - 0.2	_		
	High level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -4 \text{ mA}$	2.3	2.0	_		
				I _{OH} = -6 mA	2.3	1.8	_		
Output voltage				$I_{OH} = -8 \text{ mA}$	2.3	1.7	_		
		V _{OL} V		I _{OL} = 100 μA	2.3~2.7	_	0.2		
	Low level		٧ _{OL}	$V_{IN} = V_{IH} \ or \ V_{IL}$	I _{OL} = 6 mA	2.3	_	0.4	
				I _{OL} = 8 mA	2.3	_	0.6		
Input leakage curre	ent	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7	_	±5.0	μА	
2 state output off s	atata aurrant	1	$V_{IN} = V_{IH}$ or V_{IL}		2.3~2.7		±10.0		
3-state output off-state current		loz	V _{OUT} = 0~3.6 V		2.3~2.1	_	±10.0	μΑ	
Power off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА	
Quioscont supply	ourront	laa	$V_{IN} = V_{CC}$ or GND	$V_{IN} = V_{CC}$ or GND		_	20.0		
Quiescent supply	Juirelli	Icc	$V_{CC} \leqq (V_{IN},V_{OUT}) \leqq$	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		_	±20.0	μΑ	

DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteris	stics	Symbol	Test Condition			Min	Max	Unit
	1				V _{CC} (V)			
Input voltage	High level	V _{IH}		_	1.8~2.3	$0.7 \times V_{CC}$	_	V
input voitage	Low level	V _{IL}		_	1.8~2.3		0.2 × V _{CC}	V
	High level	Voh	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu A$	1.8	V _{CC} - 0.2		
Output voltage				$I_{OH} = -4 \text{ mA}$	1.8	1.4	_	V
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 100 \mu A$	1.8	1	0.2	
	Low level	VOL	AOF AIM OI AIF	I _{OL} = 4 mA	1.8	_	0.3	
Input leakage curre	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8	1	±5.0	μΑ
3-state output off-sta	ate current	I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0~3.6 \text{ V}$		1.8		±10.0	μΑ
Power off leakage of	urrent	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μА
Quiescent supply cu	Outcoant augusts augusts		V _{IN} = V _{CC} or GND		1.8		20.0	μА
Quiescent supply co	лтстк	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.0$	6 V	1.8		±20.0	μΛ



AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	nbol Test Condition		Min	Max	Unit
	ĺ		V _{CC} (V)			
	+		1.8	1.5	9.8	
Propagation delay time	t _{pLH} t _{pHL}	Figure 1, Figure 2	2.5 ± 0.2	8.0	5.6	ns
	фпг		3.3 ± 0.3	0.6	4.4	
	+		1.8	1.5	9.8	
3-state output enable	t _{pZL} t _{pZH}	Figure 1, Figure 3	2.5 ± 0.2	8.0	6.5	ns
			3.3 ± 0.3	0.6	5.0	
	t _{pLZ}	Figure 1, Figure 3	1.8	1.5	7.2	
3-state output disable			2.5 ± 0.2	8.0	3.9	ns
			3.3 ± 0.3	0.6	3.6	
Output to output skew	4		1.8	_	0.5	
	t _{osLH}	(Note)	2.5 ± 0.2	_	0.5	ns
	tosHL		3.3 ± 0.3	_	0.5	

For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition		Тур.	Unit	
Characteristics	Cymbol	rest solidition		V _{CC} (V)	ιyp.	Offic
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	0.15	
Quiet output maximum dynamic V _{OL}	VOLP	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	-0.15	
Quiet output minimum dynamic $V_{\mbox{OL}}$	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	-0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	-0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	1.55	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	2.65	

Note: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

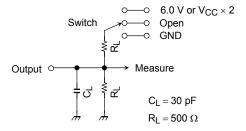
Characteristics	Symbol	Test Condition		Tun	Unit
Characteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	Offic
Input capacitance	C _{IN}	_	1.8, 2.5, 3.3	6	pF
Output capacitance	Co	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	6.0 V V _{CC} × 2	$@V_{CC} = 3.3 \pm 0.3 \text{ V} \\ @V_{CC} = 2.5 \pm 0.2 \text{ V} \\ @V_{CC} = 1.8 \text{ V}$	
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

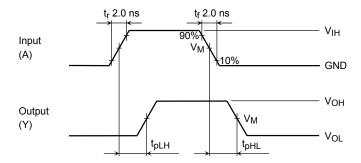


Figure 2 t_{pLH}, t_{pHL}

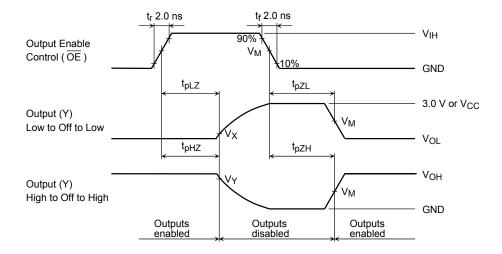
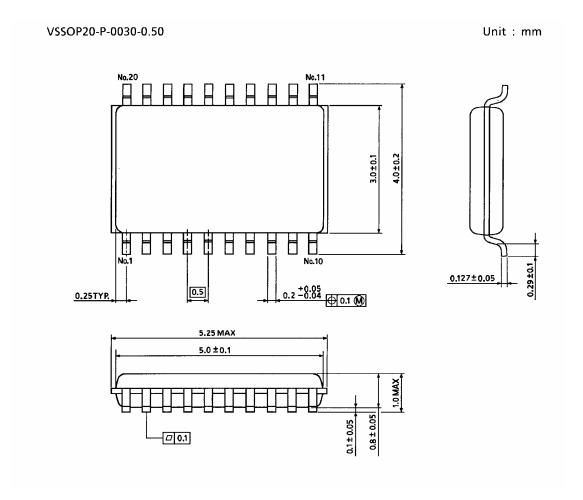


Figure 3 $\;t_{\text{pLZ}},\,t_{\text{pHZ}},\,t_{\text{pZL}},\,t_{\text{pZH}}$

Symbol		V_{CC}	
Symbol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V
V _{IH}	2.7 V	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

7 2007-10-19

Package Dimensions



Weight: 0.03 g (typ.)

RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which
 manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No
 responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
 may result from its use. No license is granted by implication or otherwise under any patents or other rights of
 TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
 compatibility. Please use these products in this document in compliance with all applicable laws and regulations
 that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
 occurring as a result of noncompliance with applicable laws and regulations.

9 2007-10-19